

This response places the above-referenced patent application in better condition for allowance, and therefore, is a proper response after final pursuant to 37 C.F.R. §1.116.

Claim 43 is cancelled. Claims 1 and 3 are amended. Claims 1, 3-5, 39-42 and 44-48 remain pending in the application.

Claim 43 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form. Claim 43 depended from independent claim 1. Claim 1 is amended to include the language of claim 43, and claim 43 is cancelled. Accordingly, claim 1, as amended, is allowable. Applicant respectfully requests allowance of claim 1 in the next office action.

Claims 3-5, 39-42 and 44-48 depend from independent claim 1, and therefore, are allowable for depending from an allowable independent claim.


This application is now believed to be in immediate condition for allowance, and action to that end is respectfully requested. If the Examiner's next anticipated action is to be anything other than a Notice of Allowance, the undersigned respectfully requests a telephone interview prior to issuance of any

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such subsequent action.

Respectfully submitted,

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Application Serial No. 09/298,160
Filing Date April 22, 1999
Inventor Dan G. Custer
Assignee Micron Technology, Inc.
Group Art Unit 1746
Examiner Allan W. Olsen
Attorney's Docket No. MI22-1172
Title: Polishing Systems, Method of Polishing Substrates, and Methods of Preparing
Liquids for Semiconductor Fabrication Processes

VERSION WITH MARKINGS TO SHOW CHANGES MADE ACCOMPANYING
RESPONSE TO FINAL OFFICE ACTION DATED APRIL 1, 2002
PURSUANT TO 37 C.F.R. §1.116

In the Claims

The claims have been amended as follows. Underlines indicate insertions
and ~~strikeouts~~ indicate deletions.

1. (Amended) A method of preparing a polishing process liquid for a
semiconductor polishing process comprising:

providing a liquid;

degassifying the liquid; ~~and~~

injecting a gas into the liquid to regassify the liquid, the regassification
increasing a total dissolved gas concentration in the liquid to greater than or
equal to 200 ppb, the regassification forming the polishing process liquid; and

wherein the injecting the gas into the degassified liquid increases the total
dissolved gas concentration in the liquid to from about 450 ppb to about 550
ppb.

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3. (Amended) The method of Claim 1 wherein the ~~providing provides~~
~~a water comprising~~ liquid comprises water.

Please cancel claim 43.

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